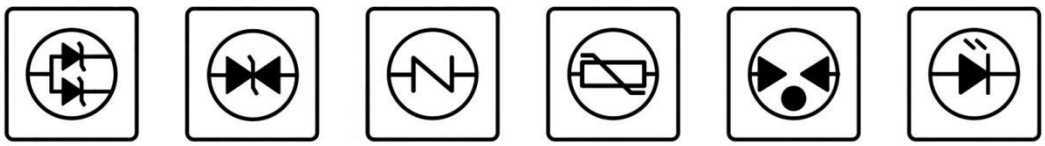
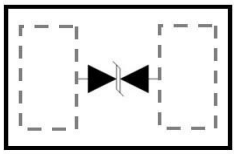
MSKSEMI
SEMICONDUCTOR



Product data sheet

PIN CONFIGURATION



DFN1006-2L

Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Features

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 85 Watts @ 8 x 20 μs Pulse
- Low Leakage current
- Response Time is Typically < 1 ns
- We declare that the material of product compliance with RoHS requirements.

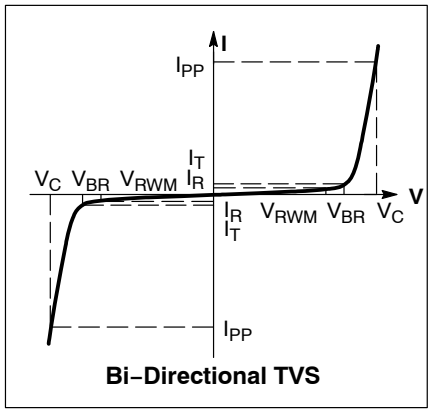
Absolute Ratings (T_{amb}=25°C)

Symbol	Parameter	Value	Units
P_{PP}	Peak Pulse Power (t_p = 8/20 μ s)	85	W
T_L	Maximum lead temperature for soldering during 10s	260	°C
T_{stg}	Storage Temperature Range	-55 to +155	°C
T_{op}	Operating Temperature Range	-40 to +150	°C
T_j	Maximum junction temperature	150	°C
	IEC61000-4-2 (ESD) air discharge	±30	KV
	contact discharge	±30	

Electrical Parameter

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
P_{pk}	Peak Power Dissipation
C	Capacitance @ V_R = 0 and f = 1.0 MHz



Electrical Characteristics

P/N	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 1)		I_T	V_C (V) @ I_{PP} = 1 A	V_C (V) @ I_{PP} = 8 A	I_{PP}(A)	P_{PK}(W)	C (pF)
	Max	Max	Min	Max	mA	Max	Max	Max	Max	Max
ESD9N5V-MS	5.0	0.5	5.6	8	1.0	8.5	9	10	85	20

*Surge current waveform per Figure 1.

1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25℃.

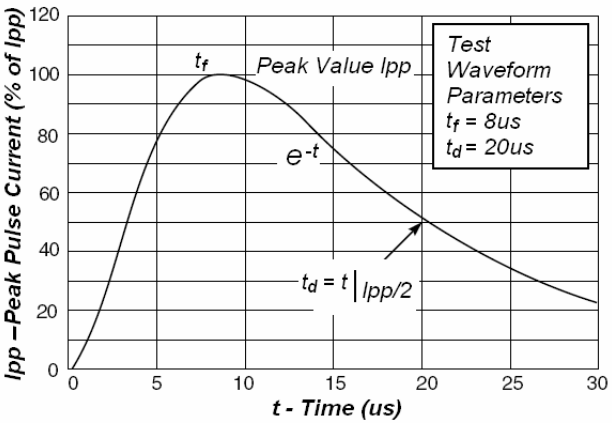


Fig1. Pulse Waveform

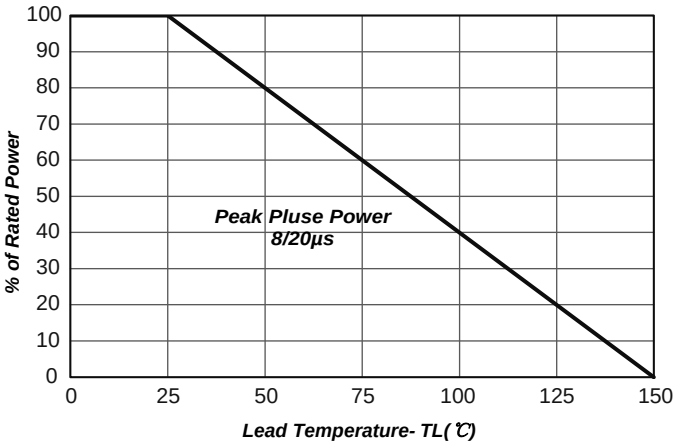
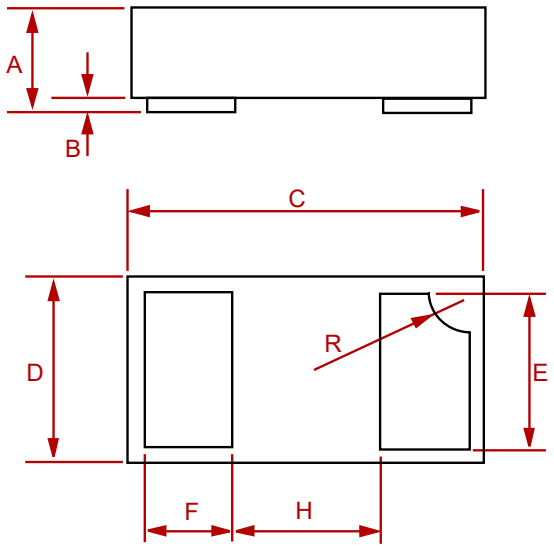


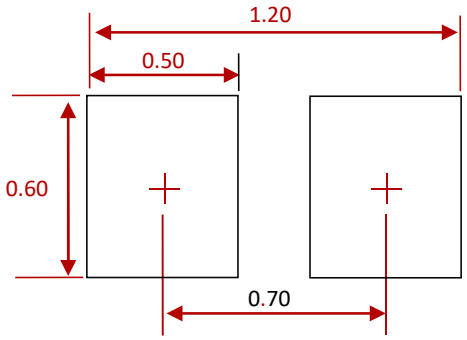
Fig2.Power Derating Curve

PACKAGE MECHANICAL DATA



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.0125	0.02	0.32	0.52
B	0.000	0.002	0.00	0.05
C	0.037	0.043	0.95	1.080
D	0.022	0.027	0.55	0.680
E	0.016	0.024	0.40	0.60
F	0.008	0.012	0.20	0.30
H	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15

Suggested Pad Layout



NOTES:

1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
ESD9N5V-MS	DFN1006-2L	10000

Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specificationsof any andall MSKSEMI Semiconductor products described orcontained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer’s products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer’sproducts orequipment.

■ MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringementsof intellectual property rights or other rightsof third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.